

Title (en)
OPTOELECTRONIC SEMICONDUCTOR COMPONENT

Title (de)
OPTOELEKTRONISCHES HALBLEITERBAUELEMENT

Title (fr)
COMPOSANT À SEMI-CONDUCTEURS OPTO-ÉLECTRONIQUE

Publication
EP 2011161 A2 20090107 (DE)

Application
EP 07722298 A 20070425

Priority

- DE 2007000740 W 20070425
- DE 102006019109 A 20060425
- DE 102006030252 A 20060630
- DE 102006061167 A 20061222

Abstract (en)
[origin: WO2007121739A2] Disclosed is an optoelectronic semiconductor component comprising a supporting substrate as well as an intermediate layer that provides adhesion between the supporting substrate and a component structure. The component structure encompasses an active layer that is used for generating radiation.

IPC 8 full level
H01L 33/46 (2010.01); **H01L 33/00** (2010.01); **H01L 33/22** (2010.01); **H01L 33/40** (2010.01)

CPC (source: EP US)
H01L 33/465 (2013.01 - EP US); **H01L 33/0093** (2020.05 - EP US); **H01L 33/22** (2013.01 - EP US); **H01L 33/405** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US); **H01L 2933/0091** (2013.01 - EP US)

Citation (search report)
See references of WO 2007121739A2

Designated contracting state (EPC)
DE

Designated extension state (EPC)
AL BA HR MK RS

DOCDB simple family (publication)
WO 2007121739 A2 20071101; **WO 2007121739 A3 20080313**; CN 101443923 A 20090527; CN 101443923 B 20101208; DE 102006061167 A1 20071220; EP 2011161 A2 20090107; JP 2009534859 A 20090924; JP 5623074 B2 20141112; KR 101370257 B1 20140305; KR 20080112410 A 20081224; TW 200746479 A 20071216; TW I354381 B 20111211; US 2009309113 A1 20091217; US 8093607 B2 20120110

DOCDB simple family (application)
DE 2007000740 W 20070425; CN 200780014703 A 20070425; DE 102006061167 A 20061222; EP 07722298 A 20070425; JP 2009506911 A 20070425; KR 20087028644 A 20070425; TW 96114217 A 20070423; US 29870307 A 20070425